

Description

The HSBA3204 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most applications.

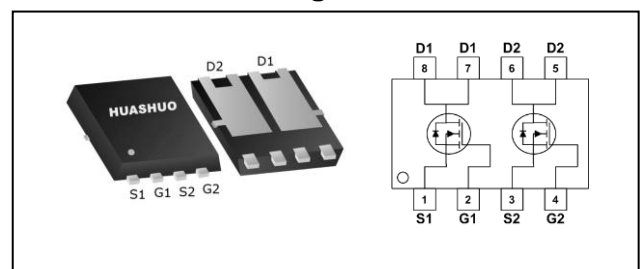
The HSBA3204 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	30	V
$R_{DS(ON),typ}$	6.5	m Ω
I_D	35	A

PRPAK5X6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	35	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	24.7	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	10.6	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	8.5	A
I_{DM}	Pulsed Drain Current ²	92	A
EAS	Single Pulse Avalanche Energy ³	57.8	mJ
I_{AS}	Avalanche Current	34	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	19.2	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	1.42	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	6.5	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.027	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =12A	---	6.5	8.5	mΩ
		V _{GS} =4.5V, I _D =10A	---	11	14	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.5	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.8	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =15A	---	38	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.7	2.9	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =12A	---	12.6	17.6	nC
Q _{gs}	Gate-Source Charge		---	4.2	5.9	
Q _{gd}	Gate-Drain Charge		---	5.1	7.1	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =12A	---	4.6	9.2	ns
T _r	Rise Time		---	12.2	22	
T _{d(off)}	Turn-Off Delay Time		---	26.6	53	
T _f	Fall Time		---	8	16	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	1317	1844	pF
C _{oss}	Output Capacitance		---	163	228	
C _{rss}	Reverse Transfer Capacitance		---	131	183	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	15	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	I _F =30A, dI/dt=100A/μs, T _J =25°C	---	9.2	---	nS
Q _{rr}	Reverse Recovery Charge		---	2	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 20Z copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=34A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

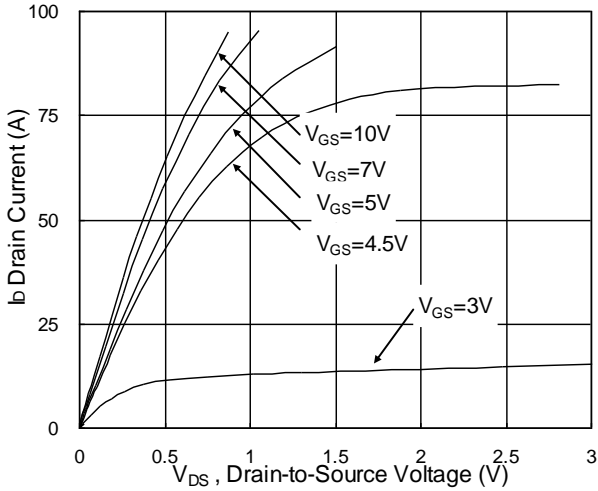


Fig.1 Typical Output Characteristics

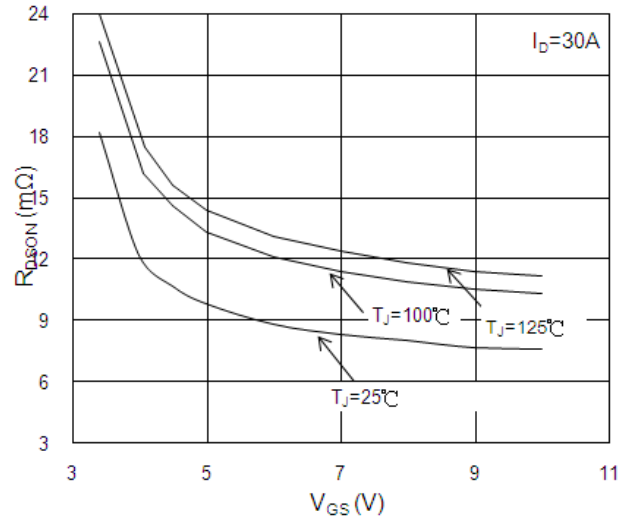


Fig.2 On-Resistance vs. Gate-Source

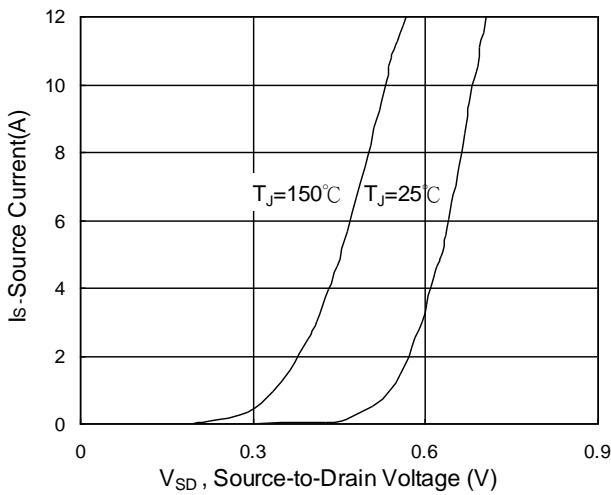


Fig.3 Forward Characteristics of reverse

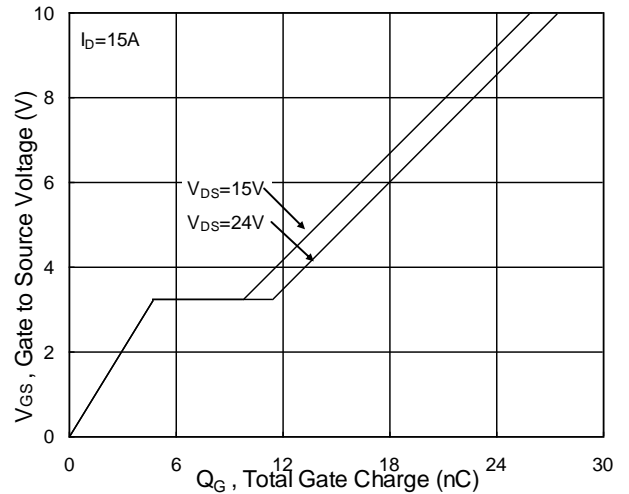


Fig.4 Gate-Charge Characteristics

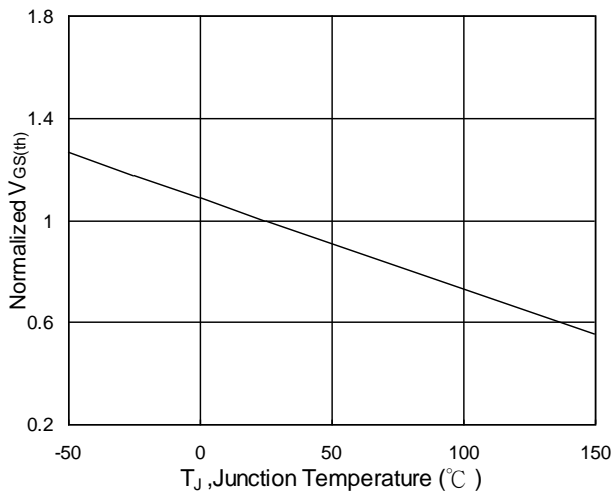


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

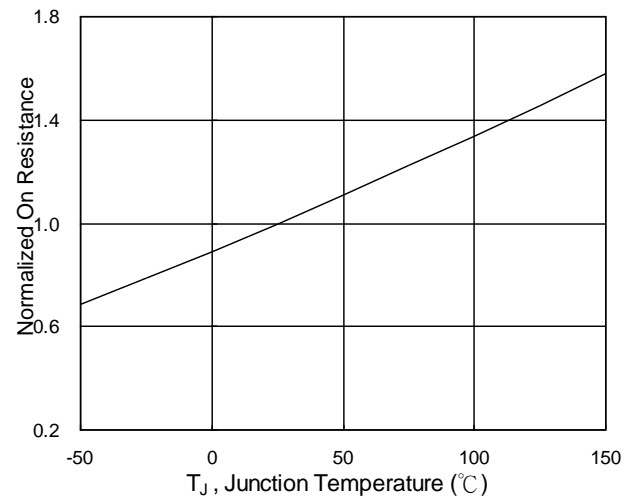


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

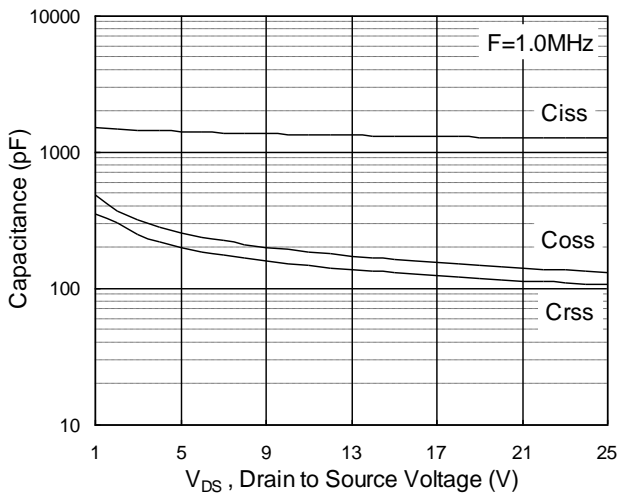


Fig.7 Capacitance

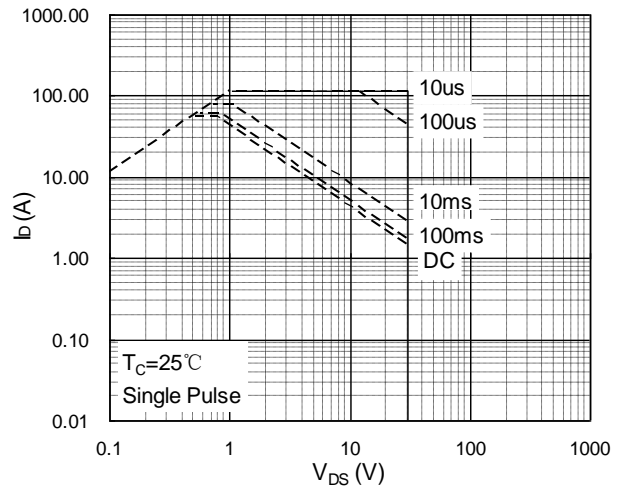


Fig.8 Safe Operating Area

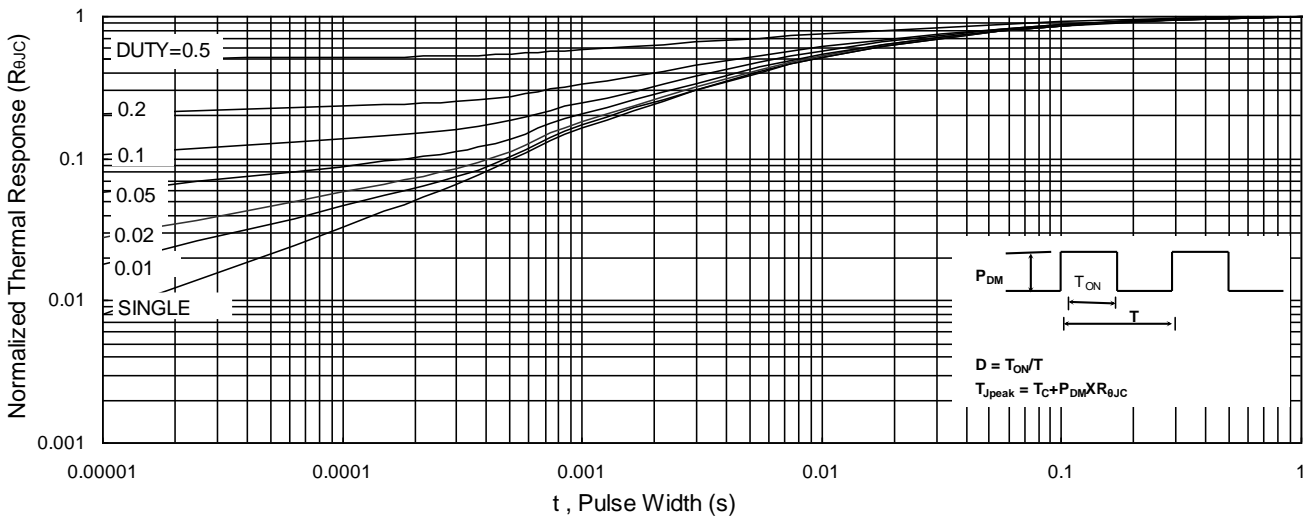


Fig.9 Normalized Maximum Transient Thermal Impedance

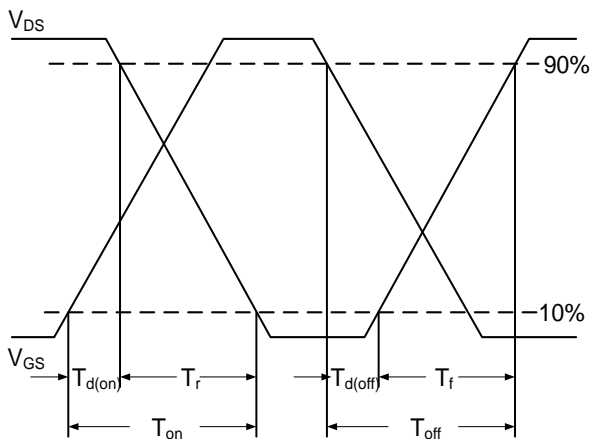


Fig.10 Switching Time Waveform

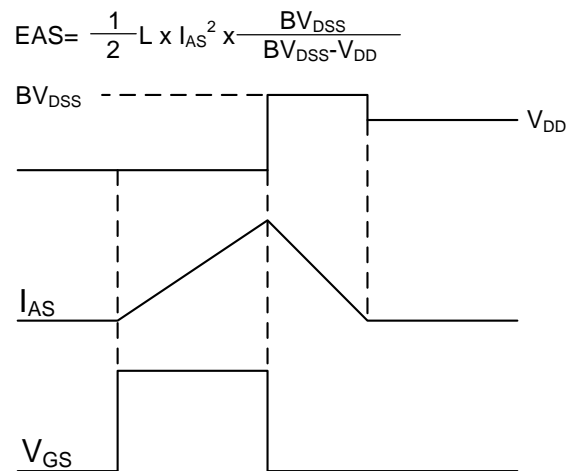
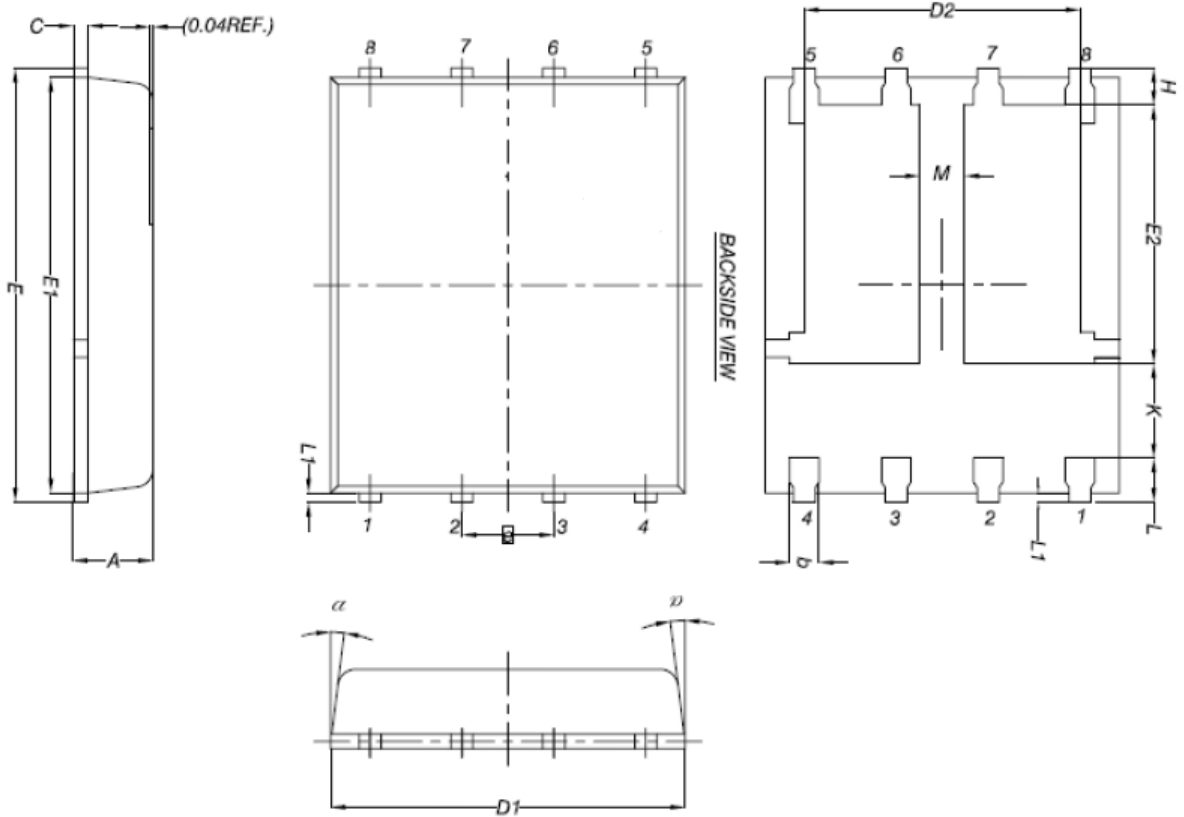


Fig.11 Unclamped Inductive Switching



PRPAK5x6-8L Dual EP2 Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.17	0.035	0.046
b	0.33	0.51	0.013	0.020
C	0.20	0.30	0.008	0.012
D1	4.80	5.20	0.189	0.205
D2	3.61	3.96	0.142	0.156
E	5.90	6.15	0.232	0.242
E1	5.70	5.85	0.224	0.230
E2	3.30	3.78	0.130	0.149
e	1.27 BSC		0.05 BSC	
H	0.38	0.61	0.015	0.024
K	1.10	---	0.043	---
L	0.38	0.61	0.015	0.024
L1	0.05	0.25	0.002	0.010
M	0.50	---	0.020	---
α	0°	12°	0°	12°

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